

N and P-Channel Enhancement Mode Power MOSFET

Description

The ECG1205 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

General Features

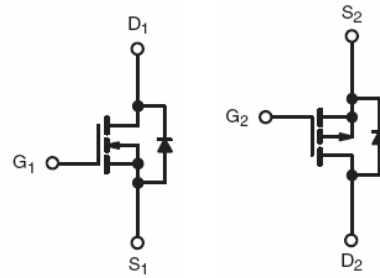
● N-Channel

- $V_{DS} = 12V, I_D = 5A$
- $R_{DS(ON)} < 32m\Omega @ V_{GS} = 4.5V$
- $R_{DS(ON)} < 42m\Omega @ V_{GS} = 2.5V$
- $R_{DS(ON)} < 80m\Omega @ V_{GS} = 1.8V$

● P-Channel

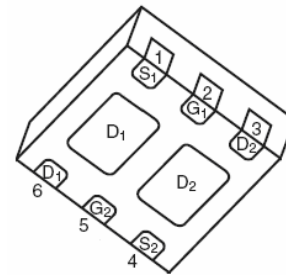
- $V_{DS} = -12V, I_D = -5A$
- $R_{DS(ON)} < 74m\Omega @ V_{GS} = -4.5V$
- $R_{DS(ON)} < 110m\Omega @ V_{GS} = -2.5V$
- $R_{DS(ON)} < 220m\Omega @ V_{GS} = -1.8V$

● Load Switch for Portable Devices



N-channel

P-channel



Pin assignment

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
1205	ECG1205	DFN2X2-6L	-	-	-

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit	
Drain-Source Voltage	V_{DS}	12	-12	V	
Gate-Source Voltage	V_{GS}	± 12	± 12	V	
Continuous Drain Current	I_D	$T_A = 25^\circ C$	5	-5	A
		$T_A = 70^\circ C$	4.5	-3.8	
Pulsed Drain Current ^(Note 1)	I_{DM}	20	-15	A	
Maximum Power Dissipation	P_D	1.9	1.9	W	
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ C$	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	N-Ch	65	$^\circ C/W$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	P-Ch	65	$^\circ C/W$

N-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	12	20	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =12V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V, V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	0.4	0.6	1	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =5A	-	28	32	mΩ
		V _{GS} =2.5V, I _D =4.6A	-	36	42	mΩ
		V _{GS} =1.8V, I _D =4.1A	-	55	80	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =5A	-	20	-	S
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =6V, V _{GS} =0V, F=1.0MHz	-	495	-	PF
Output Capacitance	C _{oss}		-	155	-	PF
Reverse Transfer Capacitance	C _{rss}		-	95	-	PF
Switching Characteristics						
Turn-on Delay Time	t _{d(on)}	V _{DD} =6V, R _L =1.2Ω V _{GS} =10V, R _{GEN} =4.5Ω	-	7.0	-	nS
Turn-on Rise Time	t _r		-	5.0	-	nS
Turn-Off Delay Time	t _{d(off)}		-	18	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Q _g	V _{DS} =6V, I _D =5A, V _{GS} =4.5V	-	6.6	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	nC
Gate-Drain Charge	Q _{gd}		-	1.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =5A	-	-	1.2	V

P-CH Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30	-33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-12V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-4.5A$	-	60	74	m Ω
		$V_{GS}=-2.5V, I_D=-3.2A$	-	84	110	m Ω
		$V_{GS}=-1.8V, I_D=-1A$	-	130	220	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-10V, I_D=-5A$	-	10	-	S
Dynamic Characteristics						
Input Capacitance	C_{ISS}	$V_{DS}=-6V, V_{GS}=0V,$ $F=1.0MHz$	-	520	-	PF
Output Capacitance	C_{OSS}		-	100	-	PF
Reverse Transfer Capacitance	C_{RSS}		-	65	-	PF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-6V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	7.5	-	nS
Turn-on Rise Time	t_r		-	5.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	19	-	nS
Turn-Off Fall Time	t_f		-	7	-	nS
Total Gate Charge	Q_g	$V_{DS}=-6V, I_D=-4.5A$ $V_{GS}=-4.5V$	-	9.2	-	nC
Gate-Source Charge	Q_{gs}		-	1.6	-	nC
Gate-Drain Charge	Q_{gd}		-	2.2	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=-5A$	-	-	-1.2	V

N- Channel Typical Electrical and Thermal Characteristics (Curves)

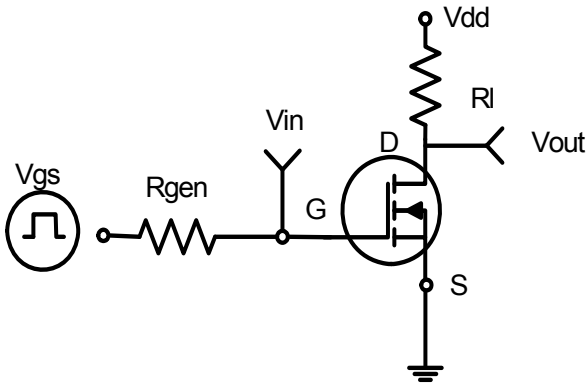


Figure 1: Switching Test Circuit

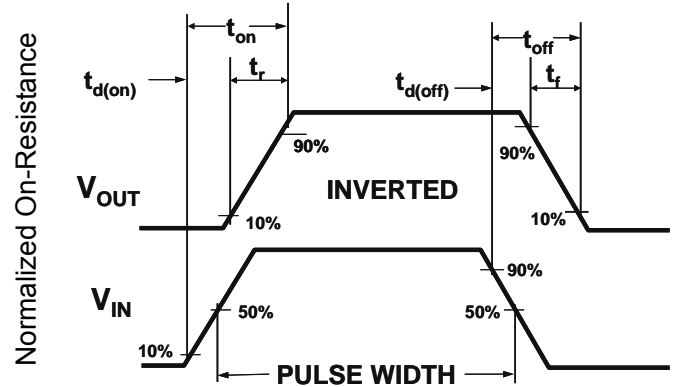


Figure 2: Switching Waveforms

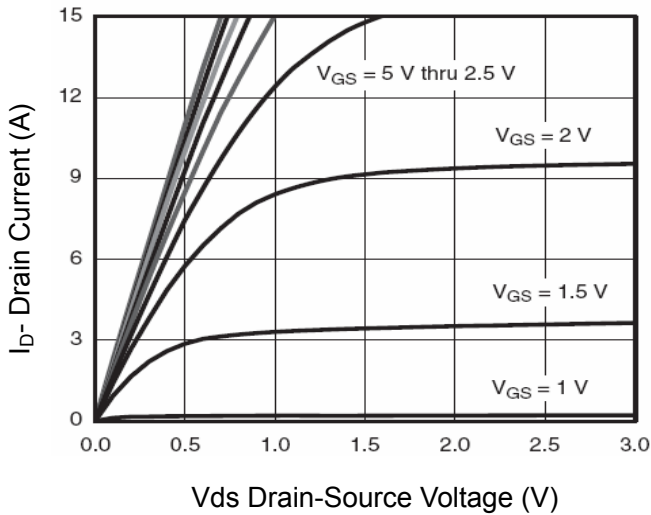


Figure 3 Output Characteristics

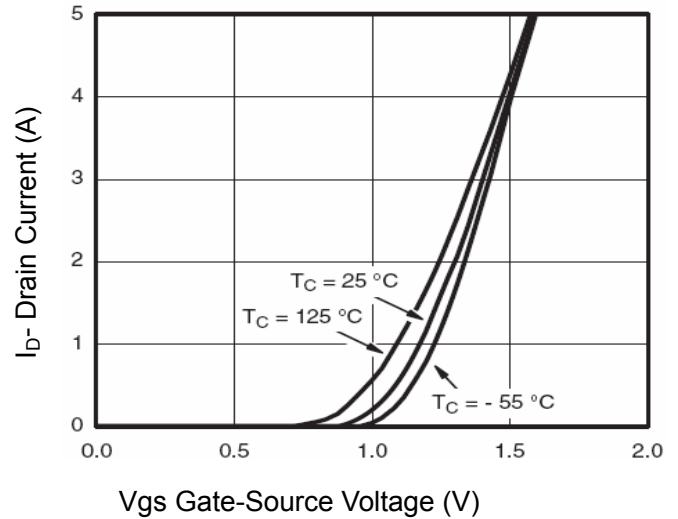


Figure 4 Transfer Characteristics

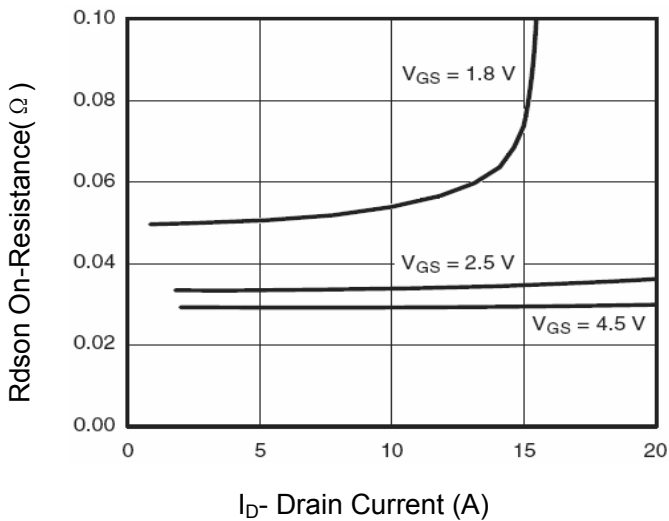


Figure 5 Drain-Source On-Resistance

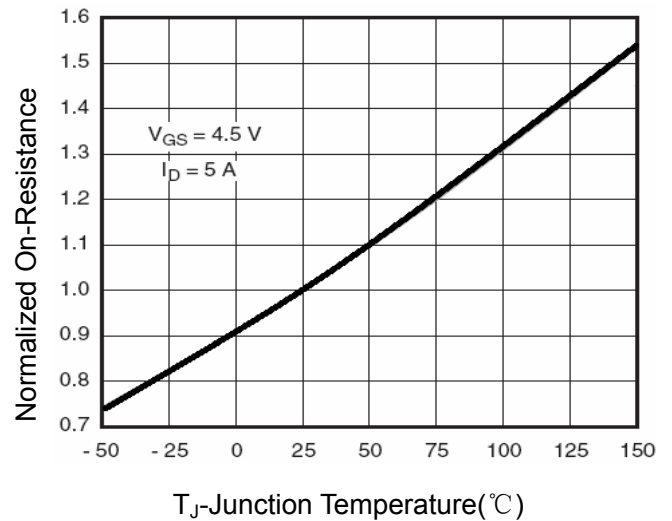
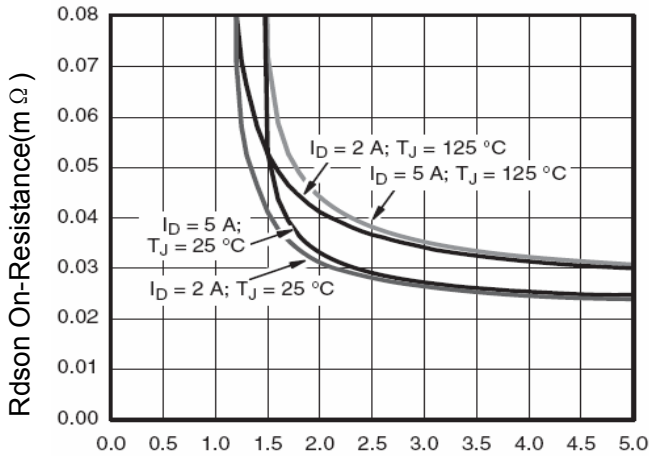
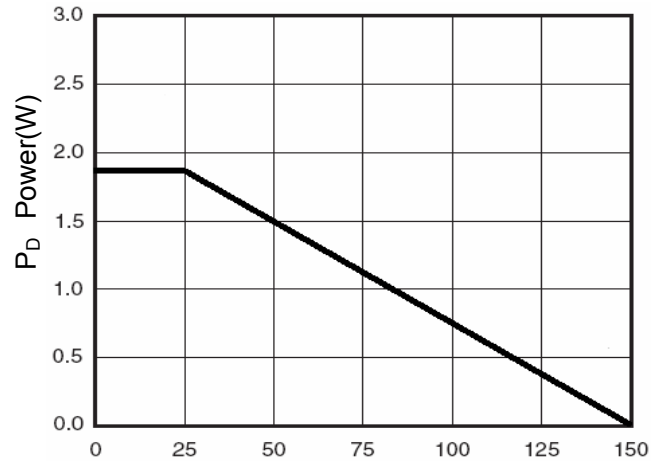


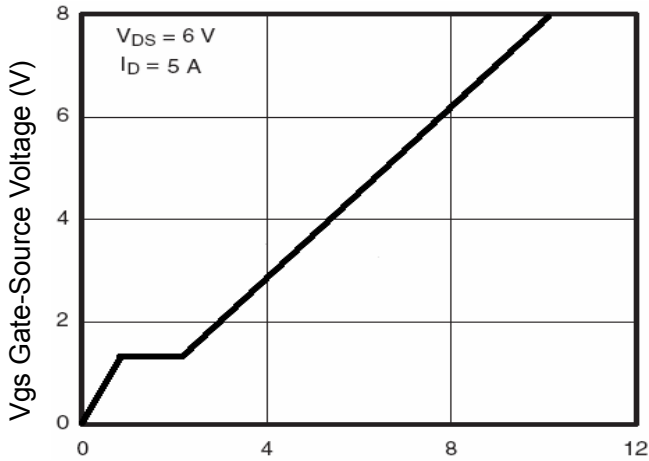
Figure 6 Drain-Source On-Resistance



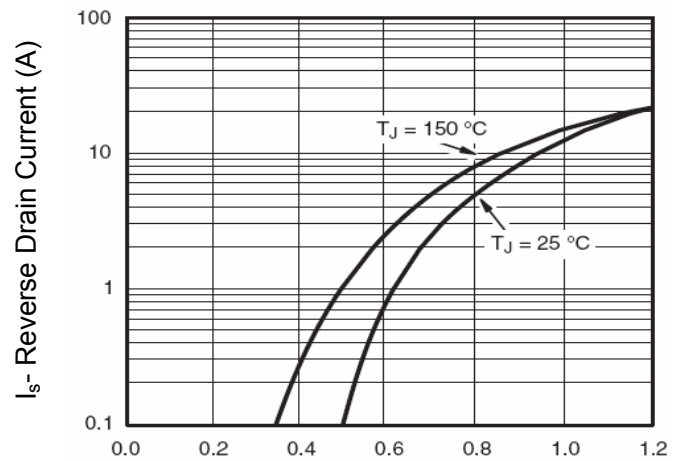
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



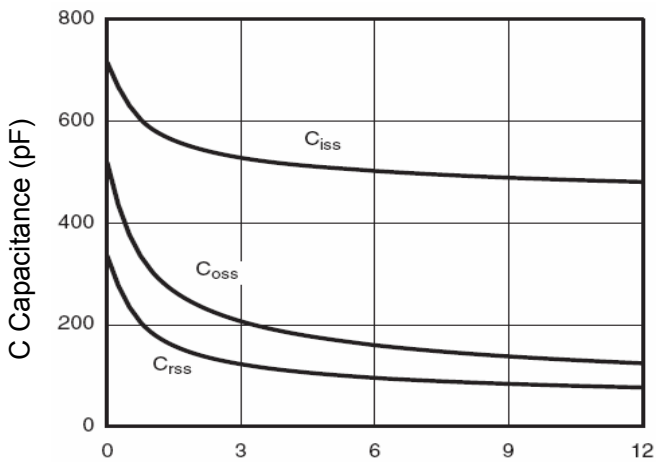
T_J-Junction Temperature(°C)
Figure 8 Power Dissipation



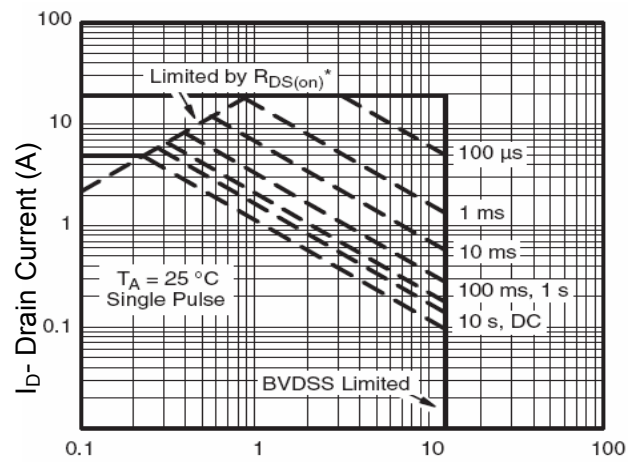
Qg Gate Charge (nC)
Figure 9 Gate Charge



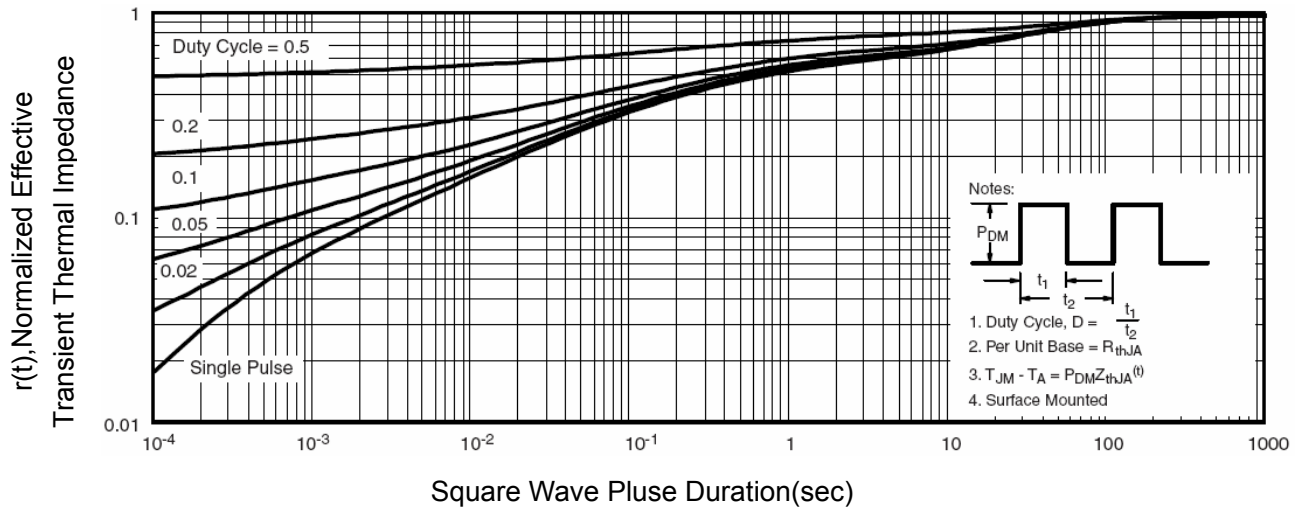
Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area



P- Channel Typical Electrical and Thermal Characteristics (Curves)

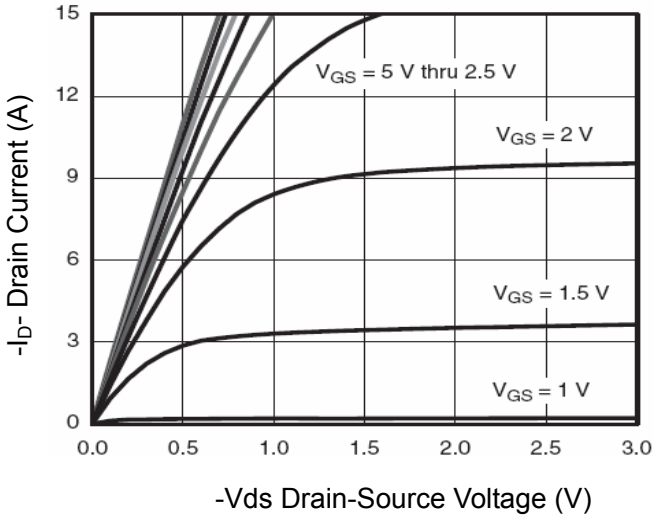


Figure 1 Output Characteristics

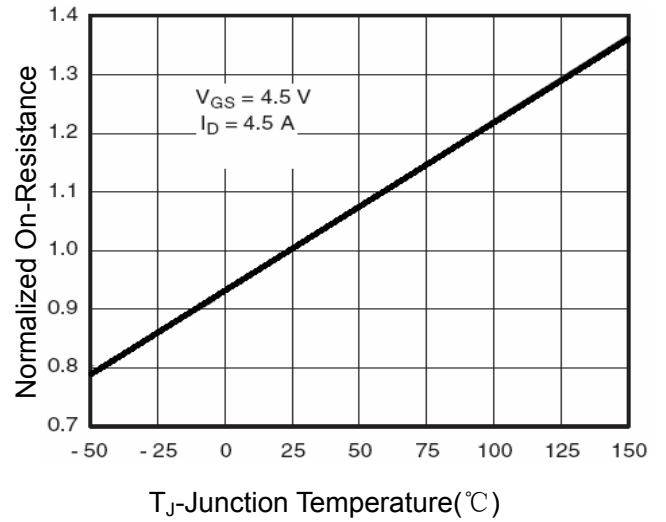


Figure 4 Rdson-Junction Temperature

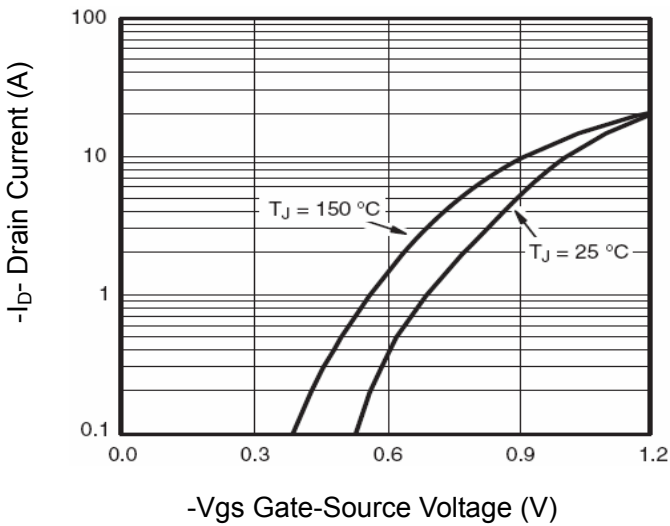


Figure 2 Transfer Characteristics

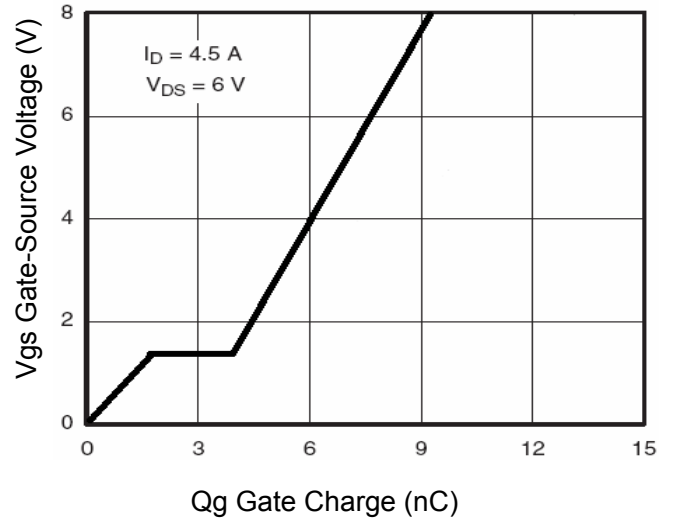


Figure 5 Gate Charge

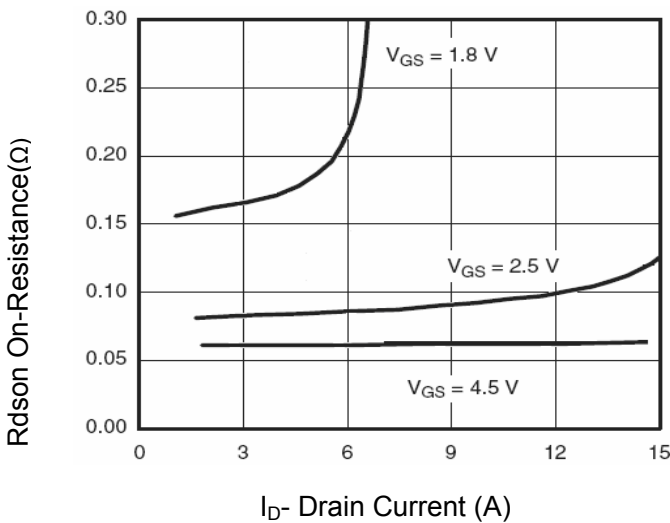


Figure 3 Rdson- Drain Current

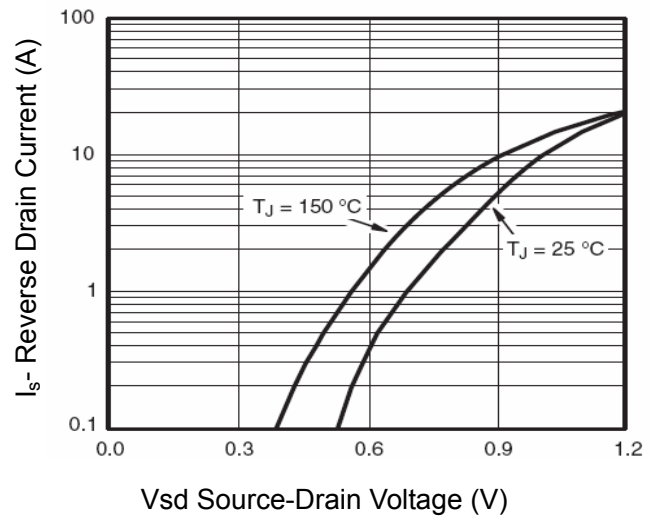


Figure 6 Source- Drain Diode Forward

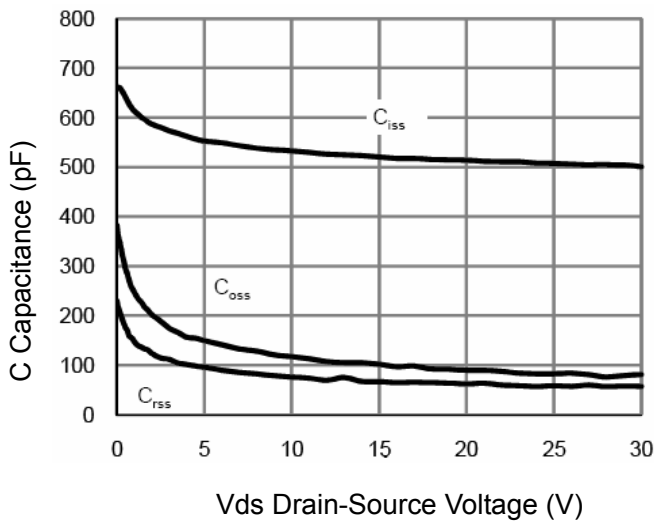


Figure 7 Capacitance vs Vds

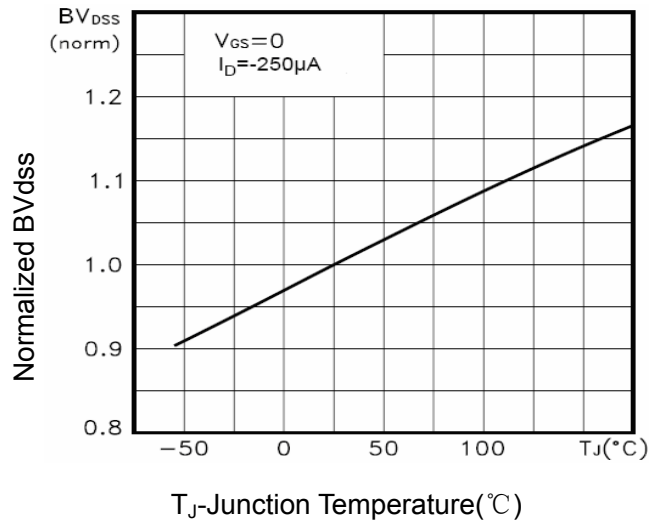


Figure 9 BV_{DSS} vs Junction Temperature

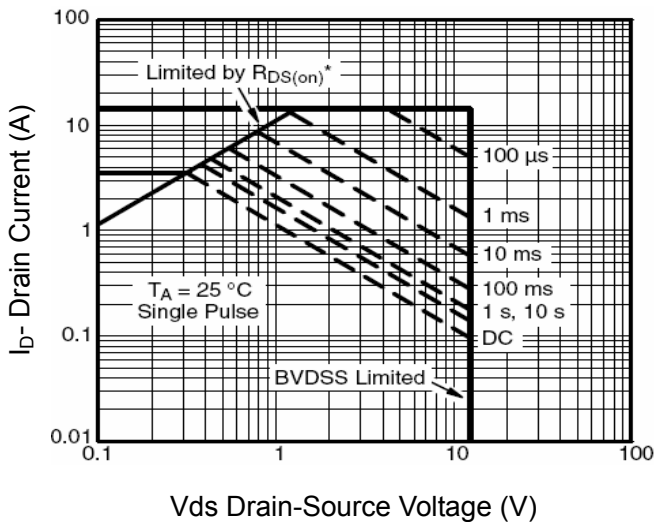


Figure 8 Safe Operation Area

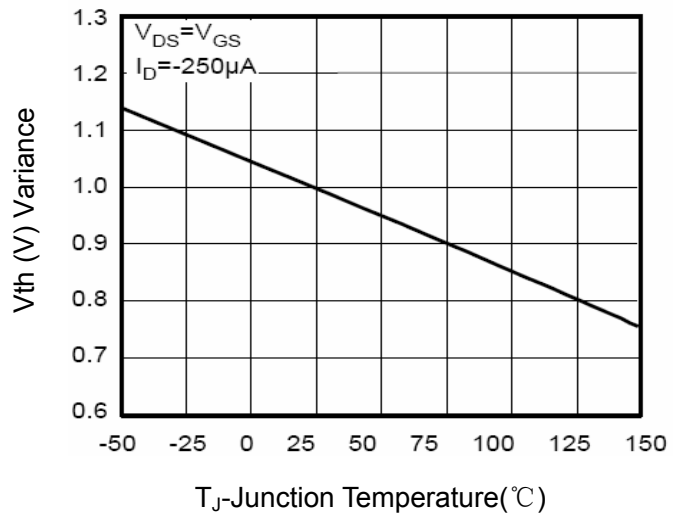


Figure 10 V_{GS(th)} vs Junction Temperature

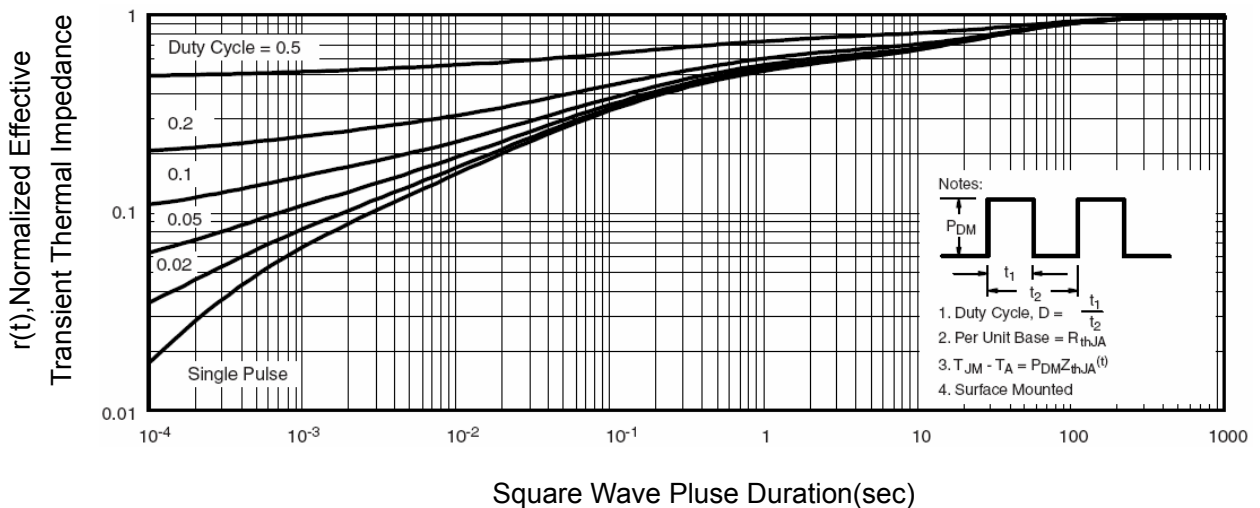
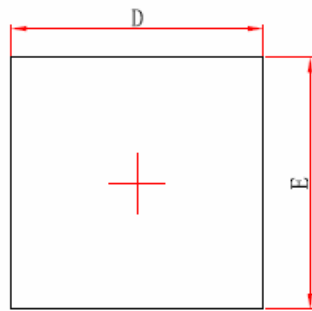
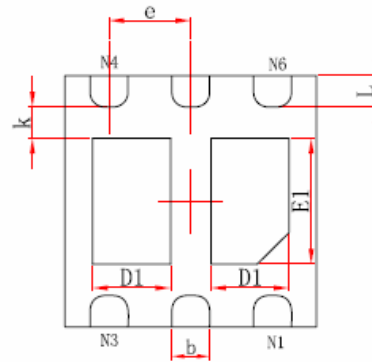


Figure 11 Normalized Maximum Transient Thermal Impedance

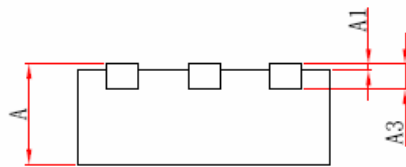
DFN2X2-6L Package Information



Top View



Bottom View



Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700/0.800	0.800/0.900	0.028/0.031	0.031/0.035
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.520	0.720	0.020	0.028
E1	0.900	1.100	0.035	0.043
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013